electrode 29 and silicon (Si). Specifically, in a case where the conductive plug 32 has the copper (Cu) film as its main constituent element, it suffices if the gate electrode 29 has as its main constituent element at least one kind of element selected from rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), and platinum (Pt), and contains as an added element at least one kind of element selected from palladium (Pd), cobalt (Co), nickel (Ni), and titanium (Ti).

IN THE CLAIMS:

Please add the following new claim:

12. A method of forming a semiconductor device having a multilayer structure comprising forming a first conductive film on a principle plane side of a semiconductor substrate, and forming a copper (Cu) film or a copper (Cu) alloy film in contact with said first conductive film, wherein said first conductive film has as a main constituent element one kind of element selected from the group consisting of at least rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), and platinum (Pt), and said first conductive film contains as an added element one kind of element selected from the group consisting of at least palladium (Pd), cobalt (Co), nickel (Ni), and titanium (Ti) with a concentration of not less than 0.14 at.% and not more than 25 at.%.

IN THE ABSTRACT:

Please amend and replace the abstract provided on a separate sheet herewith.